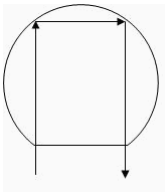
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/-1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	437.80 +/- 11.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Flatness (SBIR)	<1.00um	20mm x 20mm, no partials, b/side ref, 100% UA
	8.0	Bow	<60.00µm	ADE to ASTM F534
	9.0	Warp	<60.00µm	ADE to ASTM F657
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Carbon Concentration	< 2e16 atcm-3 new ASTM	Wafer Vendor
	14.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	15.0	Handle Thickness	420.00 +/- 10.00 µm	ADE, 100%
	16.0	Handle Doping Type	N	Wafer Vendor
	17.0	Handle Dopant	Phosphorous	Wafer Vendor
	18.0	Handle Resistivity	0.01 – 0.1 Ohm-cm	Wafer Vendor
	19.0	Backside Finish	Polished with light handling marks, oxide and laser mark.	
BuriedOxide	20.0	Oxide Type	Thermal	
	21.0	Oxide Thickness	8,000.00 +/- 800.00 A	Nanospec centre point, 4%
	22.0	Oxide formed on	Handle Wafer	
DeviceSilicon	23.0	Device Growth Method	CZ	Wafer Vendor
	24.0	Carbon Concentration	< 2e16 atcm-3 new ASTM	Wafer Vendor
	25.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor
	26.0	Nominal Thickness	17.00 +/- 1.00 µm	Filmetrics, 100% 9-Pt (note3)
	27.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	28.0	Device Doping Type	N	Wafer Vendor
	29.0	Device Dopant	Phosphorous	Wafer Vendor
	30.0	Device Resistivity	0.01 – 0.1 Ohm-cm	Wafer Vendor
	31.0	Voids	0	Bright Light, 100% (note 2)
	32.0	Scratches	none	Bright Light, 100% (note 2)
	33.0	Haze	none	Bright Light, 100% (note 2)
	34.0	LPD Count	<30 @ 0.3um	Tencor Particle Counter

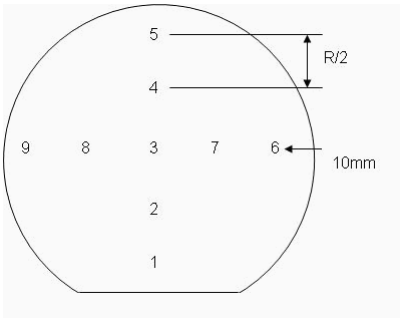
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information